HALOGEN

FREE



## Vishay Semiconductors

## Infrared Emitting Diode, 875 nm, GaAlAs



## **DESCRIPTION**

The TSHA5500 is an infrared, 875 nm emitting diode in GaAlAs on GaAlAs technology, molded in a clear, untinted plastic package.

### **FEATURES**

Package type: leaded
Package form: T-1¾
Dimensions (in mm): Ø 5
Leads with stand-off

• Peak wavelength:  $\lambda_D = 875 \text{ nm}$ 

· High reliability

• Angle of half intensity:  $\varphi = \pm 24^{\circ}$ 

· Low forward voltage

- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

### **APPLICATIONS**

- Infrared remote control and free air data transmission systems with comfortable radiation angle
- This emitter is dedicated to systems with panes in transmission space between emitter and detector, because of the low absorbtion of 875 nm radiation in glass

PRODUCT SUMMARY					
COMPONENT	I <sub>e</sub> (mW/sr)	φ (deg)	λ <sub>P</sub> (nm)	t <sub>r</sub> (ns)	
TSHA5500	30	± 24	875	600	

### Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
TSHA5500	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾	

### Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V <sub>R</sub>	5	V	
Forward current		I <sub>F</sub>	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I <sub>FM</sub>	200	mA	
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	2.5	Α	
Power dissipation		P <sub>V</sub>	180	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T <sub>amb</sub>	- 40 to + 85	°C	
Storage temperature range		T <sub>stg</sub>	- 40 to + 100	°C	
Soldering temperature	$t \le 5$ s, 2 mm from case	T <sub>sd</sub>	260	°C	
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R <sub>thJA</sub>	230	K/W	

### Note

 $T_{amb}$  = 25 °C, unless otherwise specified

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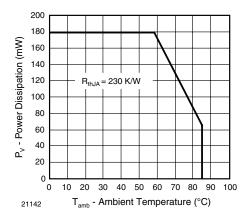


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

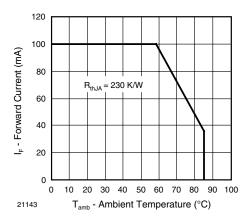


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Farmend and the me	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V <sub>F</sub>		1.5	1.8	V
Forward voltage	$I_F = 1 \text{ A}, t_p = 100 \mu \text{s}$	V <sub>F</sub>		2.8	3.5	V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 100 mA	TK <sub>VF</sub>		- 1.6		mV/K
Reverse current	V <sub>R</sub> = 5 V	I <sub>R</sub>			100	μΑ
Junction capacitance	$V_R = 0 \text{ V, } f = 1 \text{ MHz, } E = 0$	Cj		20		pF
Dodient intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l <sub>e</sub>	16	30	48	mW/sr
Radiant intensity	$I_F = 1 \text{ A}, t_p = 100 \mu \text{s}$	l <sub>e</sub>	128	240		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	фе		24		mW
Temperature coefficient of φ <sub>e</sub>	I <sub>F</sub> = 20 mA	TKφe		- 0.7		%/K
Angle of half intensity		φ		± 24		deg
Peak wavelength	I <sub>F</sub> = 100 mA	$\lambda_{p}$		875		nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ		80		nm
Temperature coefficient of $\lambda_p$	I <sub>F</sub> = 100 mA	TKλ <sub>p</sub>		0.2		nm/K
Disations	I <sub>F</sub> = 100 mA	t <sub>r</sub>		600		ns
Rise time	I <sub>F</sub> = 1 A	t <sub>r</sub>		300		ns
Fall time	I <sub>F</sub> = 100 mA	t <sub>f</sub>		600		ns
	I <sub>F</sub> = 1 A	t <sub>f</sub>		300		ns
Virtual source diameter		d		2.2		mm

### Note

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## **BASIC CHARACTERISTICS**

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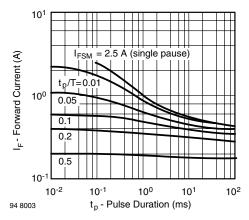


Fig. 3 - Pulse Forward Current vs. Pulse Duration

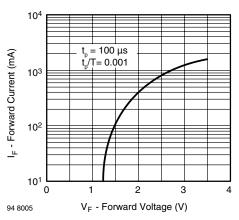


Fig. 4 - Forward Current vs. Forward Voltage

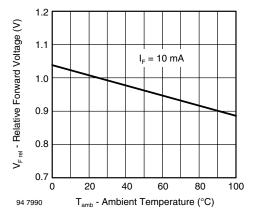


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

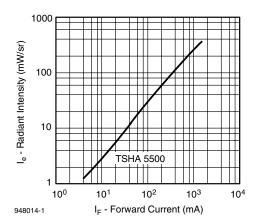


Fig. 6 - Radiant Intensity vs. Forward Current

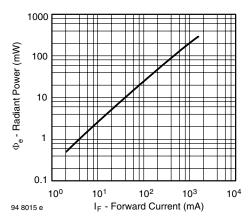


Fig. 7 - Radiant Power vs. Forward Current

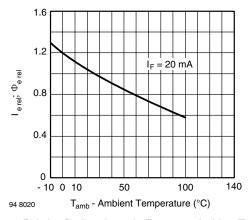


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

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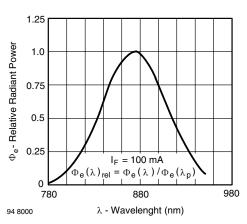


Fig. 9 - Relative Radiant Power vs. Wavelength

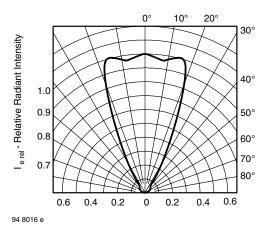
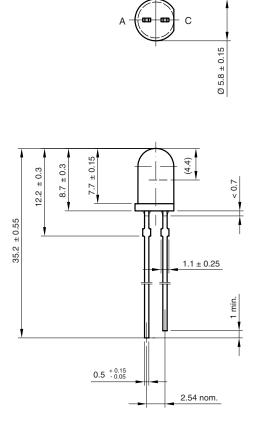
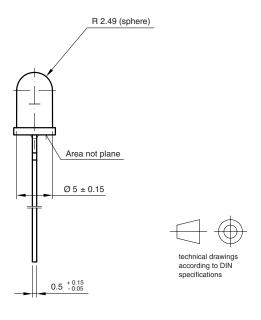


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

## **PACKAGE DIMENSIONS** in millimeters



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